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**INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT**

Applicant: TEN BERGE et al.

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Examiner: Unknown Group Art Unit: Unknown

**U.S. PATENT DOCUMENTS**

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
	AR					
	BR					
	CR					
	DR					
	ER					
	FR					
	GR					

**FOREIGN PATENT DOCUMENTS**

	Document Number	Date MM/YYYY	Country	Inventor Name	English Abstract		Translation Readily Available	
					Enclosed	No	Enclose	No
	HR							
	IR							
	JR							
	KR							

**OTHER (Including in this order: Author, Title, Periodical Name, Date, Pertinent Pages, etc.)**

LR	Mattias Vangbo et al., High Precision Crystallographic Alignment of InP(100), Electrochemical and Solid-State Letters, 2(8) 1999, pp. 407-408.			
MR	G. Ensell, Alignment of mask patterns to crystal orientation, Sensors and Actuators A 53, (1996) pp. 345-348.			
NR	Mattias Vangbo et al., Precise mask alignment to the crystallographic orientation of silicon wafers using wet anisotropic etching, J. Micromech. Microeng. 6 (1996) pp. 279-284.			
OR	J. M. Lai et al., Precision alignment of mask etching with respect to crystal orientation, J. Micromech. Microeng. 8 (1998) pp. 327-329.			
PR				
QR				

Examiner: *[Signature]* Date Considered: 4/11/2007

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.